

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Please amend the claims as follows:

Claims 1-8 (previously canceled)

9. (currently amended) A semiconductor device comprising:
a semiconductor substrate, the semiconductor substrate including a plurality of device structures thereon, and a buried layer in the semiconductor substrate; and
an interconnect on the semiconductor substrate, the interconnect comprising at least one slot provided in the semiconductor substrate and at least one a plurality of metals within the slot wherein the plurality of metals comprises three metals, wherein the first and second metals fill the slot and the third metal provides an interconnect layer, wherein the at least one slot is oxidized everywhere except at the bottom of the slot, and the interconnect forms a sinker to the buried layer.

Please cancel claims 10-12.

10. (cancelled)

11. (cancelled)

12. (cancelled)
13. (currently amended) A high voltage interconnect on a semiconductor substrate, the substrate including a buried layer comprising:
 - a slot provided in the semiconductor substrate; and
 - ~~at least one a plurality of metals within the slot wherein the plurality of metals comprises three metals, wherein the first and second metals fill the slot and the third metal provides an interconnect layer~~, wherein the at least one slot is oxidized everywhere except at the bottom of the slot, and the interconnect forms a sinker to the buried layer.
- Please cancel claims 14-16.
14. (cancelled)
15. (cancelled)
16. (cancelled)
17. (currently amended) The interconnect of claim ~~42~~ 13 wherein the sinker can be coupled to a collector on a drain of a device to ensure lowest resistance.

18. (currently amended) The interconnect of claim ~~16~~ 13 wherein the slot with oxide completely around the three deposited layers is coupled to an emitter of a bipolar device which provides a high current carrying connection to the emitter.

19. (currently amended) The interconnect of claim ~~16~~ 13 wherein the slot with oxide completely around the three deposited layers is coupled to a source MOS transistor which provides a high current carrying connection to the source.

20. (currently amended) The interconnect of claim ~~16~~ 13 wherein there are a plurality of slots filled with three depositions of metal.

21. (original) The interconnect of claim 20 wherein the plurality of slots are coupled to the emitters, collectors, drains, sources of Bipolar transistors and MOS transistors on the same device, thus forming high current carrying conductors on a same device while limiting the area consumed on the surface to a maximum width of a slot.

22. (original) The interconnect of claim 21 wherein the high current carrying conductors are on the same level of metal resulting in thick metal obtained vertically in the substrate, while limiting the space on the surface of the device and not requiring additional planarization.